

Christoforos G Theodorou

List of Publications by Year in descending order

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all docs

63
docs citations

63
times ranked

615
citing authors

#	ARTICLE	IF	CITATIONS
1	Parasitic Coupling in 3D Sequential Integration: The Example of a Two-Layer 3D Pixel. Technologies, 2022, 10, 38.	5.1	1
2	“Pinch to Detect”: A Method to Increase the Number of Detectable RTN Traps in Nano-scale MOSFETs. , 2021, , .		1
3	Restricted Channel Migration in 2D Multilayer ReS ₂ . ACS Applied Materials & Interfaces, 2021, 13, 19016-19022.	8.0	13
4	Impact of Hot Carrier Aging on the 1/f and Random Telegraph Noise of Short-Channel Triple-Gate Junctionless MOSFETs. IEEE Transactions on Device and Materials Reliability, 2021, 21, 348-353.	2.0	7
5	VERILOR: A Verilog-A Model of Lorentzian Spectra for Simulating Trap-related Noise in CMOS Circuits. , 2021, , .		2
6	Impact of Hot Carrier Aging on the Performance of Triple-Gate Junctionless MOSFETs. IEEE Transactions on Electron Devices, 2020, 67, 424-429.	3.0	5
7	Inter-tier electrostatic coupling effects in 3D sequential integration devices and circuits. Solid-State Electronics, 2020, 168, 107715.	1.4	2
8	Performance and Low-Frequency Noise of 22-nm FDSOI Down to 4.2 K for Cryogenic Applications. IEEE Transactions on Electron Devices, 2020, 67, 4563-4567.	3.0	27
9	A Method for Series-Resistance-Immune Extraction of Low-Frequency Noise Parameters in Nanoscale MOSFETs. IEEE Transactions on Electron Devices, 2020, 67, 4568-4572.	3.0	5
10	Optimization of GOPS-Based Functionalization Process and Impact of Aptamer Grafting on the Si Nanonet FET Electrical Properties as First Steps towards Thrombin Electrical Detection. Nanomaterials, 2020, 10, 1842.	4.1	4
11	Effect of Gate Structure on the Trapping Behavior of GaN Junctionless FinFETs. IEEE Electron Device Letters, 2020, 41, 832-835.	3.9	18
12	Influence of series resistance on the experimental extraction of FinFET noise parameters. , 2020, , .		1
13	Effects of Contact Potential and Sidewall Surface Plane on the Performance of GaN Vertical Nanowire MOSFETs for Low-Voltage Operation. IEEE Transactions on Electron Devices, 2020, 67, 1547-1552.	3.0	7
14	Noise and Fluctuations in Fully Depleted Silicon-on-Insulator MOSFETs. , 2020, , 33-85.		6
15	Intermittency-induced criticality in the random telegraph noise of nanoscale UTBB FD-SOI MOSFETs. Microelectronic Engineering, 2019, 216, 111027.	2.4	9
16	1/f noise analysis in high mobility polymer-based OTFTs with non-fluorinated dielectric. Applied Physics Letters, 2019, 114, .	3.3	7
17	Upgrade of Drain Current Compact Model for Nanoscale Triple-Gate Junctionless Transistors to Continuous and Symmetric. IEEE Transactions on Electron Devices, 2019, 66, 4486-4489.	3.0	4
18	Charge Pumping in Ultrathin SOI Tunnel FETs: Impact of Back-Gate Voltage. ECS Transactions, 2019, 89, 111-120.	0.5	1

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19	Low-Frequency Noise Characteristics of GaN Nanowire Gate-All-Around Transistors With/Without 2-DEG Channel. IEEE Transactions on Electron Devices, 2019, 66, 1243-1248.	3.0	16
20	Impact of Inter-Tier Coupling on Static and Noise Performance in 3D Sequential Integration Technology. , 2019, , .		2
21	Static and low frequency noise characterization of ultra-thin body InAs MOSFETs. Solid-State Electronics, 2018, 143, 56-61.	1.4	4
22	Impact of Low-Temperature Coolcubeâ„¢ Process on the Performance of FDSOI Tunnel FETs. , 2018, , .		0
23	A Self-contained Defect-aware Module for Realistic Simulations of LFN, RTN and Time-dependent Variability in FD-SOI Devices and Circuits. , 2018, , .		3
24	1/f Noise Characterization of Piezoresistive Nano-Gauges for MEMS Sensors. , 2018, , .		0
25	Origin of Low-Frequency Noise in Triple-Gate Junctionless n-MOSFETs. IEEE Transactions on Electron Devices, 2018, 65, 5481-5486.	3.0	5
26	Static and Low Frequency Noise Characterization of InGaAs MOSFETs and FinFETs on Insulator. , 2018, , .		7
27	Low-frequency noise in surface-treated AlGaIn/GaN HFETs. , 2018, , .		0
28	Chaotic Behavior of Random Telegraph Noise in Nanoscale UTBB FD-SOI MOSFETs. IEEE Electron Device Letters, 2017, 38, 517-520.	3.9	7
29	All Operation Region Characterization and Modeling of Drain and Gate Current Mismatch in 14-nm Fully Depleted SOI MOSFETs. IEEE Transactions on Electron Devices, 2017, 64, 2080-2085.	3.0	22
30	Comparison for $1/f$ Noise Characteristics of AlGaIn/GaN FinFET and Planar MISHFET. IEEE Transactions on Electron Devices, 2017, 64, 3634-3638.	3.0	29
31	Statistical low-frequency noise characterization in sub-15 nm Si/SiGe nanowire Trigate pMOSFETs. , 2017, , .		0
32	Drain current local variability from linear to saturation region in 28nm bulk NMOSFETs. Solid-State Electronics, 2017, 128, 31-36.	1.4	3
33	Drain current local variability from linear to saturation region in 28nm bulk NMOSFETs. , 2016, , .		3
34	Influence of AC signal oscillator level on effective mobility measurement by split Câ€“V technique in MOSFETs. Electronics Letters, 2016, 52, 1492-1493.	1.0	2
35	Study of Hot-Carrier-Induced Traps in Nanoscale UTBB FD-SOI MOSFETs by Low-Frequency Noise Measurements. IEEE Transactions on Electron Devices, 2016, , 1-7.	3.0	8
36	Characterization and Modeling of NBTI in Nanoscale UltraThin Body UltraThin Box FD-SOI MOSFETs. IEEE Transactions on Electron Devices, 2016, 63, 4913-4918.	3.0	7

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37	Noise-induced dynamic variability in nano-scale CMOS SRAM cells. , 2016, , .		4
38	Low frequency noise variability in ultra scaled FD-SOI n-MOSFETs: Dependence on gate bias, frequency and temperature. Solid-State Electronics, 2016, 117, 88-93.	1.4	17
39	Hot carrier degradation modeling of short-channel n-FinFETs suitable for circuit simulators. Microelectronics Reliability, 2016, 56, 10-16.	1.7	11
40	Hot-carrier degradation model for nanoscale ultra-thin body ultra-thin box SOI MOSFETs suitable for circuit simulators. Microelectronic Engineering, 2016, 159, 9-16.	2.4	7
41	New LFN and RTN analysis methodology in 28 and 14nm FD-SOI MOSFETs. , 2015, , .		11
42	Drain-Current Flicker Noise Modeling in nMOSFETs From a 14-nm FDSOI Technology. IEEE Transactions on Electron Devices, 2015, 62, 1574-1579.	3.0	23
43	Low frequency noise statistical characterization of 14nm FDSOI technology node. , 2015, , .		4
44	Hot carrier degradation mechanisms of short-channel FDSOI n-MOSFETs. , 2015, , .		1
45	Dynamic variability in 14nm FD-SOI MOSFETs and transient simulation methodology. Solid-State Electronics, 2015, 111, 100-103.	1.4	3
46	Full gate voltage range Lambert-function based methodology for FDSOI MOSFET parameter extraction. Solid-State Electronics, 2015, 111, 123-128.	1.4	42
47	Impact of Source-Drain Series Resistance on Drain Current Mismatch in Advanced Fully Depleted SOI n-MOSFETs. IEEE Electron Device Letters, 2015, 36, 433-435.	3.9	25
48	Analytical Compact Model for Lightly Doped Nanoscale Ultrathin-Body and Box SOI MOSFETs With Back-Gate Control. IEEE Transactions on Electron Devices, 2015, 62, 3117-3124.	3.0	16
49	Full front and back gate voltage range method for the parameter extraction of advanced FDSOI CMOS devices. , 2015, , .		0
50	Impact of low-frequency noise variability on statistical parameter extraction in ultra-scaled CMOS devices. Electronics Letters, 2014, 50, 1393-1395.	1.0	6
51	Statistical analysis of dynamic variability in 28nm FD-SOI MOSFETs. , 2014, , .		9
52	Evolution of low frequency noise and noise variability through CMOS bulk technology nodes from 0.5 μ m down to 20nm. Solid-State Electronics, 2014, 95, 28-31.	1.4	18
53	Low-Frequency Noise Sources in Advanced UTBB FD-SOI MOSFETs. IEEE Transactions on Electron Devices, 2014, 61, 1161-1167.	3.0	40
54	Analytical Modeling of Threshold Voltage and Interface Ideality Factor of Nanoscale Ultrathin Body and Buried Oxide SOI MOSFETs With Back Gate Control. IEEE Transactions on Electron Devices, 2014, 61, 969-975.	3.0	19

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55	Origin of the low-frequency noise in n-channel FinFETs. Solid-State Electronics, 2013, 82, 21-24.	1.4	16
56	Short Channel Effects on LTPS TFT Degradation. Journal of Display Technology, 2013, 9, 747-754.	1.2	10
57	Low-frequency noise behavior of n-channel UTBB FD-SOI MOSFETs. , 2013, , .		7
58	Flicker noise in n-channel nanoscale tri-gate fin-shaped field-effect transistors. Applied Physics Letters, 2012, 101, .	3.3	10
59	Front-back gate coupling effect on 1/f noise in ultra-thin Si film FDSOI MOSFETs. , 2012, , .		8
60	Impact of front-back gate coupling on low frequency noise in 28 nm FDSOI MOSFETs. , 2012, , .		12
61	Symmetrical unified compact model of short-channel double-gate MOSFETs. Solid-State Electronics, 2012, 69, 55-61.	1.4	19
62	Origin of Low-Frequency Noise in the Low Drain Current Range of Bottom-Gate Amorphous IGZO Thin-Film Transistors. IEEE Electron Device Letters, 2011, 32, 898-900.	3.9	29
63	Analytical low-frequency noise model in the linear region of lightly doped nanoscale double-gate metal-oxide-semiconductor field-effect transistors. Journal of Applied Physics, 2010, 108, 064512.	2.5	7